

Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 15 (original). A semiconductor component, comprising:

a semiconductor body having a substrate of a first conduction type and a first layer of a second conduction type located above said substrate;

a channel zone of said first conduction type formed in said first layer;

a first terminal zone of said second conduction type configured adjacent said channel zone;

a second terminal zone of said first conduction type formed in said first layer;

compensation zones of said first conduction type formed in said first layer; and

a second layer of said second conduction type configured between said substrate and said compensation zones.

Claim 16 (original). The semiconductor component according to claim 15, comprising:

a boundary zone of said first conduction type extending vertically in said first layer towards said semiconductor body.

Claim 17 (original). The semiconductor component according to claim 16, wherein said boundary zone extends from said channel zone to said substrate.

Claim 18 (original). The semiconductor component according to claim 16, wherein said boundary zone is laterally spaced away from said channel zone.

Claim 19 (original). The semiconductor component according to claim 18, wherein:

said semiconductor body has a first surface; and

said boundary zone extends from said first surface of said semiconductor body to said substrate.

Claim 20 (original). The semiconductor component according to claim 15, wherein said compensation zones have a pillar-shaped design.

Claim 21 (original). The semiconductor component according to claim 20, wherein at least some of said compensation zones adjoin said channel zone.

Claim 22 (original). The semiconductor component according to claim 15, wherein said compensation zones have a spherical design.

Claim 23 (original). The semiconductor component according to claim 15, wherein:

said compensation zones define first compensation zones;

said first layer has second compensation zones of said second conduction type formed therein;

said second compensation zones are adjacent said first compensation zones; and

said second compensation zones are doped more heavily than said second layer.

Claim 24 (original). The semiconductor component according to claim 15, wherein said boundary zone is doped more heavily than said substrate.

Claim 25 (original). The semiconductor component according to claim 15, wherein:

said second terminal zone has a first section extending vertically to said second layer; and

said second layer laterally extends at a level;

said second terminal zone has a second section extending laterally at said level of said second layer.

Claim 26 (original). The semiconductor component according to claim 25, wherein said first section and said second section of said second terminal zone form a well-like structure enclosing said first terminal zone and at least some of said compensation zones.

Claim 27 (original). The semiconductor component according to claim 15, wherein:

said second terminal zone has a first section extending vertically to said second layer; and

said second terminal zone has a second section extending laterally near said second layer.

Claim 28 (original). The semiconductor component according to claim 27, wherein said first section and said second section of said second terminal zone form a well-like structure enclosing said first terminal zone and at least some of said compensation zones.

Claim 29 (original). The semiconductor component according to claim 15, wherein said first layer has a number of dopant atoms of said first conduction type and a number of dopant atoms of said second conduction type that are approximately identical.

Claim 30 (currently amended). A semiconductor component, comprising:

a semiconductor body having a substrate of a first conduction type and a first layer of a second conduction type located above said substrate;

a second layer of said second conduction type formed between said first layer and said substrate, said second layer being doped more weakly than said first layer; and

a boundary zone of said first conduction type, said boundary zone vertically extending to said substrate and to said second layer; and

a plurality of compensation zones of said first conduction type formed in said first layer.